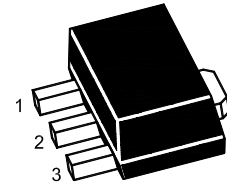


2SA1662U

PNP Silicon Epitaxial Planar Transistor

General purpose application



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

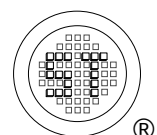
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

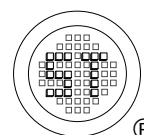
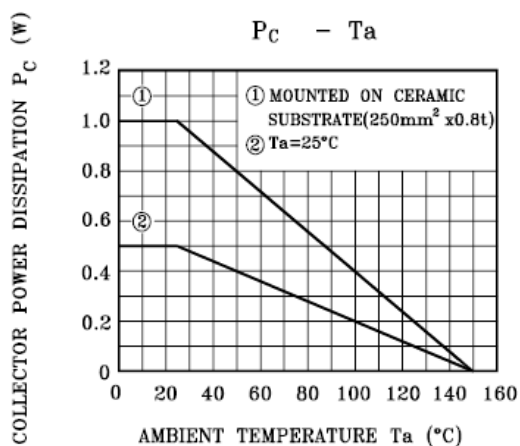
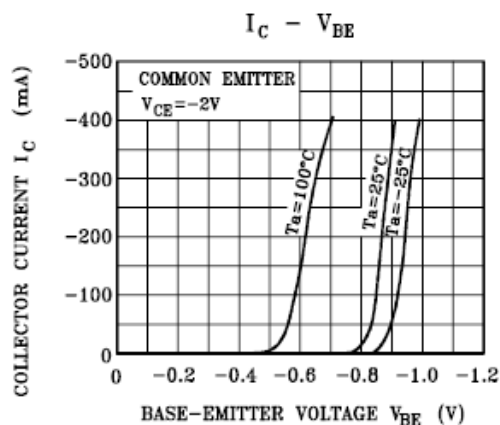
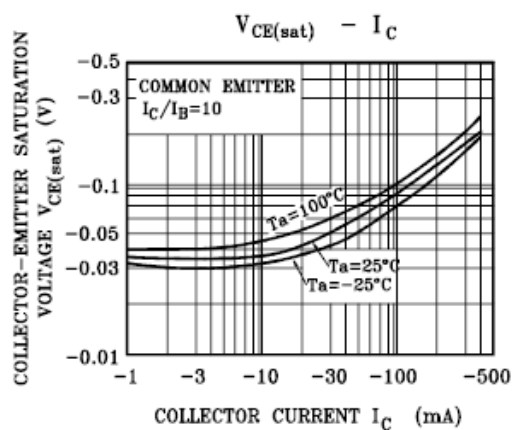
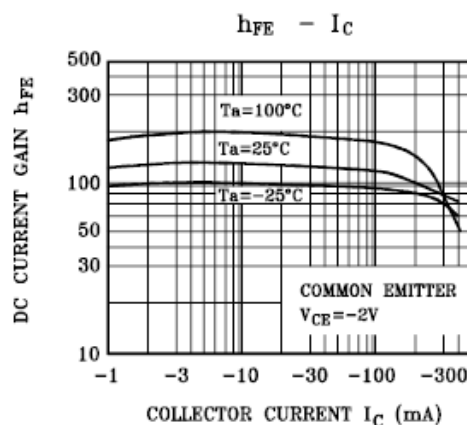
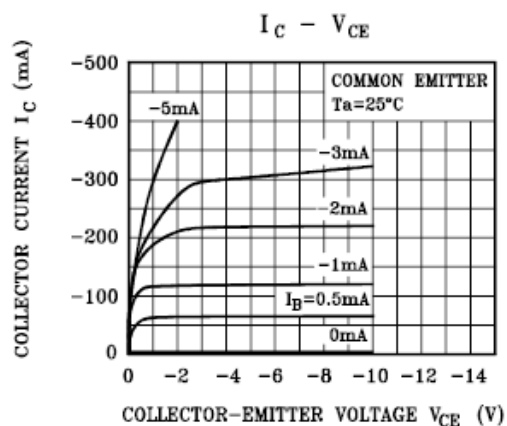
Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	80	V
Collector Emitter Voltage	$-V_{CEO}$	80	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	400	mA
Base Current	$-I_B$	80	mA
Total Power Dissipation	P_{tot}	0.5 1 ¹⁾	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

¹⁾ When mounted on a 250 mm² x 0.8 t ceramic substrate.

Characteristics at $T_a = 25^\circ\text{C}$

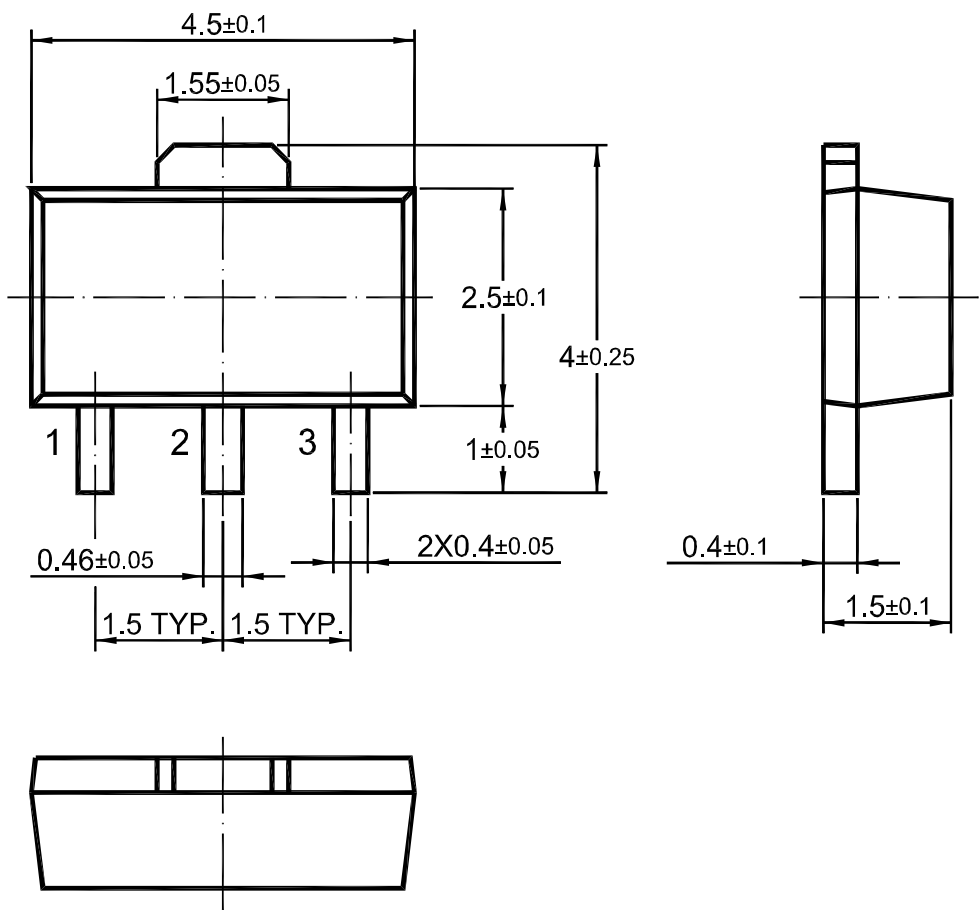
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 50\text{ mA}$ at $-V_{CE} = 2\text{ V}$, $-I_C = 200\text{ mA}$ Current Gain Group O Y	h_{FE}	70	-	140	-
	h_{FE}	120	-	240	-
	h_{FE}	40	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 80\text{ V}$	$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	100	nA
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	80	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 200\text{ mA}$, $-I_B = 20\text{ mA}$	$-V_{CE(sat)}$	-	-	0.4	V
Base Emitter on Voltage at $-V_{CE} = 2\text{ V}$, $-I_C = 5\text{ mA}$	$-V_{BE(on)}$	0.55	-	0.8	V
Transition Frequency at $-V_{CE} = 10\text{ V}$, $-I_C = 10\text{ mA}$	f_T	-	120	-	MHz
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	14	-	pF





2SA1662U

SOT-89 PACKAGE OUTLINE



Dimensions in mm

